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[Vishay Semiconductor/Diodes Division](#)
[VS-1EFH01W-M3-18](#)

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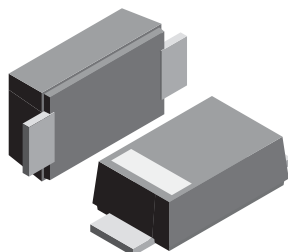


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VS-1EFH01W-M3

Vishay Semiconductors

Hyperfast Rectifier, 1 A FRED Pt®



SMF (DO-219AB)



FEATURES

- Hyperfast recovery time, reduced Q_{rr} , and soft recovery
- 175 °C maximum operating junction temperature
- Low forward voltage drop
- Low leakage current
- Specific for output and snubber operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY	
Package	DO-219AB (SMF)
$I_{F(AV)}$	1 A
V_R	100 V
V_F at I_F	0.93 V
t_{rr}	25 ns
T_J max.	175 °C
Diode variation	Single die

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		100	V
Average rectified forward current	$I_{F(AV)}$	$T_C = 160\text{ °C}$ ⁽¹⁾	1	A
Non-repetitive peak surge current	I_{FSM}	$T_J = 25\text{ °C}$	40	
Operating junction and storage temperatures	T_J, T_{Stg}		-65 to 175	°C

Note

⁽¹⁾ Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100\ \mu\text{A}$	100	-	-	V
Forward voltage	V_F	$I_F = 1\ \text{A}$	-	0.87	0.93	
		$I_F = 1\ \text{A}, T_J = 125\text{ °C}$	-	0.74	0.8	
Reverse leakage current	I_R	$V_R = V_R$ rated	-	-	2	μA
		$T_J = 125\text{ °C}, V_R = V_R$ rated	-	0.5	8	
Junction capacitance	C_T	$V_R = 100\ \text{V}$	-	5	-	pF



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	I _F = 1.0 A, di _F /dt = 50 A/μs, V _R = 30 V	-	26	-	ns
		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A	-	-	25	
		T _J = 25 °C	-	16	-	
		T _J = 125 °C	-	23	-	
Peak recovery current	I _{RRM}	T _J = 25 °C	-	1.6	-	A
		T _J = 125 °C	-	2.5	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C	-	13	-	nC
		T _J = 125 °C	-	30	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	
Approximate weight				0.015		g
				0.0005		oz.
Marking device		Case style SMF (DO-219AB)		AH		

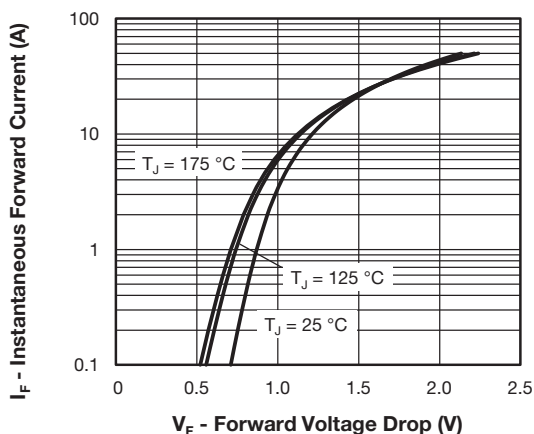


Fig. 1 - Typical Forward Voltage Drop Characteristics

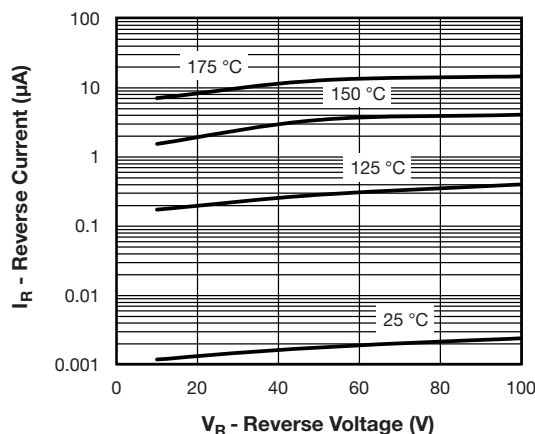


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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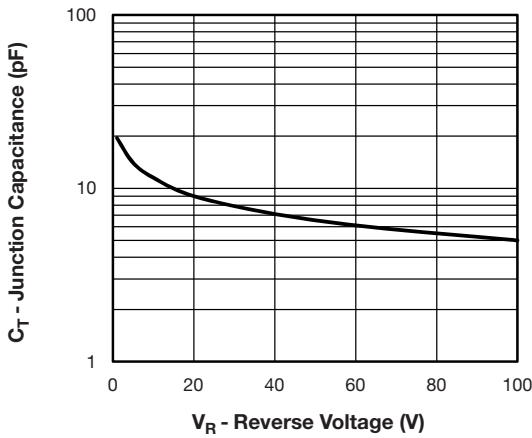


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

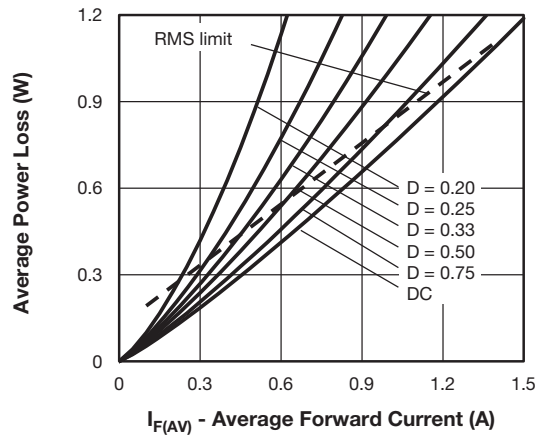


Fig. 5 - Forward Power Loss Characteristics

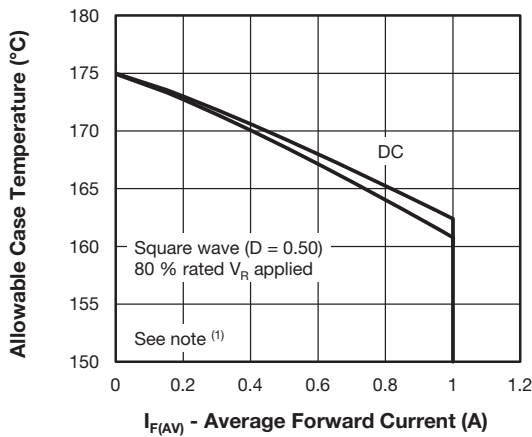


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

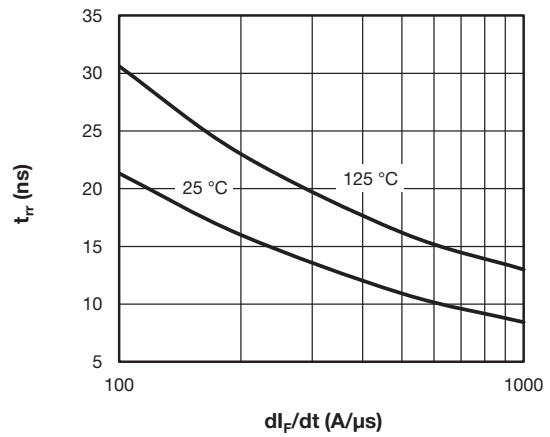


Fig. 6 - Typical Reverse Recovery Time vs. di_F/dt

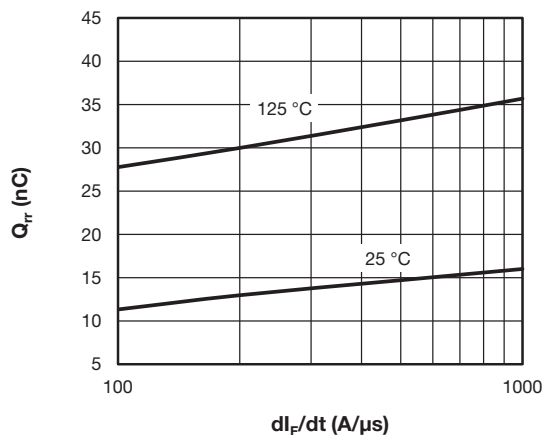


Fig. 7 - Typical Stored Charge vs. di_F/dt

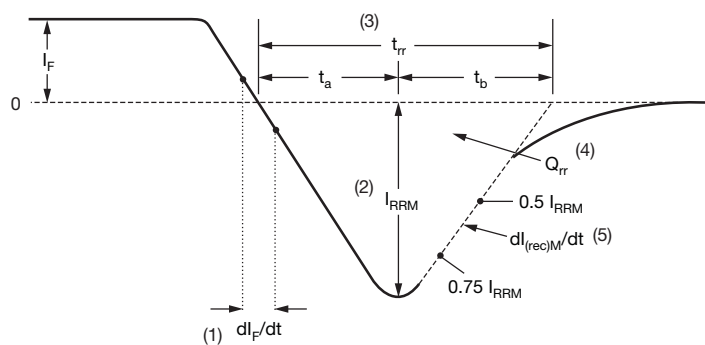
Note

- (1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
- Pd = Forward Power Loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see Fig. 6);
- Pd_{REV} = Inverse Power Loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R



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- (1) di_F/dt - rate of change of current through zero crossing
- (2) I_{RRM} - peak reverse recovery current
- (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}
- (5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-1EFH01W-M3-18	10 000	10 000	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95572
Part marking information	www.vishay.com/doc?95563
Packaging information	www.vishay.com/doc?95577

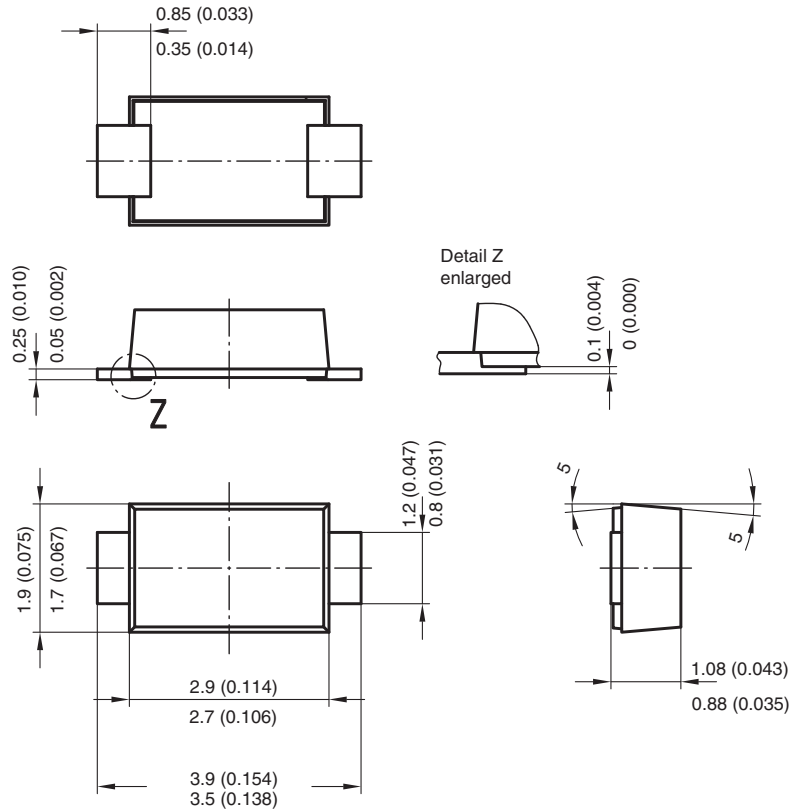


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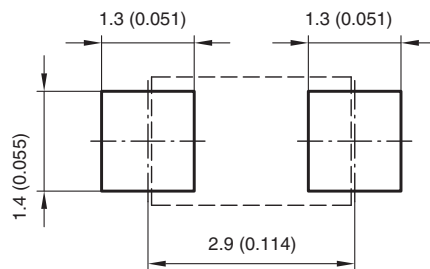
Outline Dimensions
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DO-219AB (SMF)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



Created - Date: 15. February 2005
 Rev. 3 - Date: 13. March 2007
 Document no.:S8-V-3915.01-001 (4)
 17247



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